

# Midium Power Transistors (-50V / -4A) <sup>2SAR543D</sup>

#### Structure

PNP Silicon epitaxial planar transistor

#### • Features

1) Low saturation voltage

 $V_{CE (sat)}$  = -0.4V (Max.) (I<sub>C</sub> / I<sub>B</sub>=-2A / -100mA)

2) High speed switching

## Applications

Driver

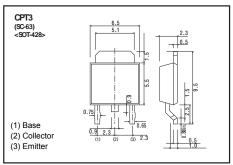
# • Packaging specifications

	Package	CPT3
Туре	Code	TL
	Basic ordering unit (pieces)	2500

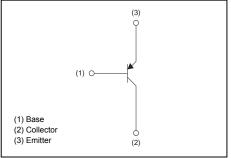
# •Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V <sub>CBO</sub>	-50	V
Collector-emitter voltage		V <sub>CEO</sub>	-50	V
Emitter-base voltage	ge	V <sub>EBO</sub>	-6	V
Collector current	DC	Ι <sub>C</sub>	-4	А
	Pulsed	I <sub>CP</sub> *1	-8	А
Power dissipation	Power dissinction		1	W
		P <sub>D</sub> *3	10	W
Junction temperatu	ure	Tj	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to 150	°C

#### • Dimensions (Unit : mm)



#### • Inner circuit (Unit : mm)



\*1 Pw=10ms, Single Pulse

\*2 Mounted on a substrate

\*3 T<sub>C</sub>=25°C

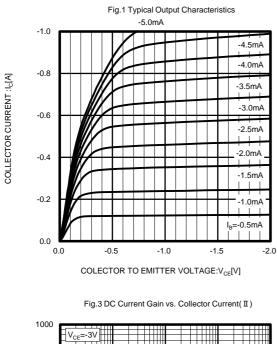
# •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	$BV_{CEO}$	-50	-	-	V	I <sub>C</sub> = -1mA
Collector-base breakdown voltage	$BV_{CBO}$	-50	-	-	V	Ι <sub>c</sub> = -100μΑ
Emitter-base breakdown voltage	$BV_{EBO}$	-6	-	-	V	Ι <sub>Ε</sub> = -100μΑ
Collector cut-off current	I <sub>CBO</sub>	-	-	-1	μA	V <sub>CB</sub> = -50V
Emitter cut-off current	I <sub>EBO</sub>	-	-	-1	μA	V <sub>EB</sub> = -4V
Collector-emitter staturation voltage	V <sub>CE(sat)</sub> <sup>*</sup> 1	-	-200	-400	mV	I <sub>C</sub> = -2A, I <sub>B</sub> = -100mA
DC current gain	h <sub>FE</sub>	180	-	450	-	V <sub>CE</sub> = -3V, I <sub>C</sub> = -100mA
Transition frequency	$f_{T}^{*1}$	-	300	-	MHz	V <sub>CE</sub> = -10V I <sub>E</sub> =300mA, f=100MHz
Collector output capacitance	C <sub>ob</sub>	-	35	-	pF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0A f=1MHz
Turn-on time	t <sub>on</sub> * <sub>2</sub>	-	45	-	ns	- 20   - 200mA
Storage time	t <sub>stg</sub> * <sub>2</sub>	-	250	-	ns	I <sub>C</sub> = -2A, I <sub>B1</sub> = -200mA, I <sub>B2</sub> =200mA, V <sub>CC</sub> <u>~</u> -10V
Fall time	t <sub>f</sub> *2	-	40	-	ns	

\*1 Pulsed

\*2 See switching time test circuit

# •Electrical characteristic curves (Ta=25°C)



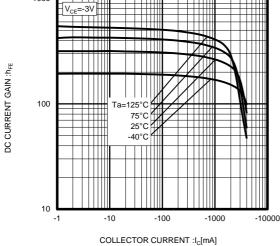


Fig.5 Collector-Emitter Saturation Voltage vs.Collector Current ( II )

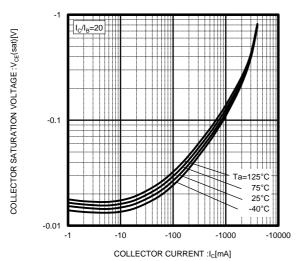


Fig.2 DC Current Gain vs. Collector Current ( I )

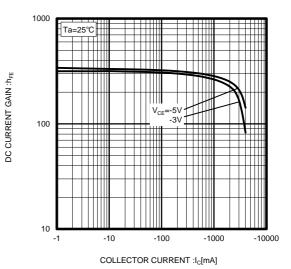
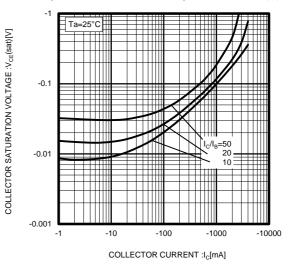
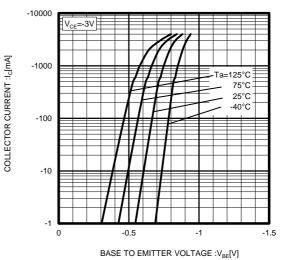


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current(I)







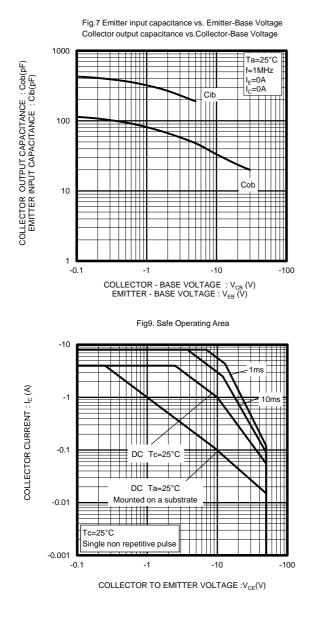
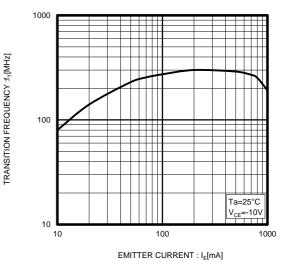
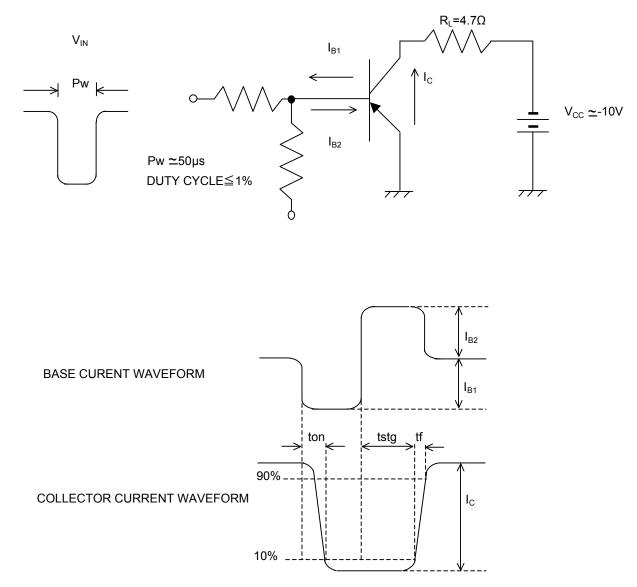


Fig8. Gain Bandwidth Product vs. Emitter Current



# • Switching time test circuit



	copying or reproduction of this document, in part or in whole, is permitted without the nsent of ROHM Co.,Ltd.
The	e content specified herein is subject to change for improvement without notice.
"Pr	e content specified herein is for the purpose of introducing ROHM's products (hereinafte oducts"). If you wish to use any such Product, please be sure to refer to the specifications ich can be obtained from ROHM upon request.
illu	amples of application circuits, circuit constants and any other information contained herein strate the standard usage and operations of the Products. The peripheral conditions mus taken into account when designing circuits for mass production.
Ho	eat care was taken in ensuring the accuracy of the information specified in this document wever, should you incur any damage arising from any inaccuracy or misprint of such prmation, ROHM shall bear no responsibility for such damage.
exa imp oth	e technical information specified herein is intended only to show the typical functions of an amples of application circuits for the Products. ROHM does not grant you, explicitly o plicitly, any license to use or exercise intellectual property or other rights held by ROHM and er parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the e of such technical information.
equ	e Products specified in this document are intended to be used with general-use electronic upment or devices (such as audio visual equipment, office-automation equipment, commu ation devices, electronic appliances and amusement devices).
The	e Products specified in this document are not designed to be radiation tolerant.
	ile ROHM always makes efforts to enhance the quality and reliability of its Products, a oduct may fail or malfunction for a variety of reasons.
aga fail sha	ase be sure to implement in your equipment using the Products safety measures to guard ainst the possibility of physical injury, fire or any other damage caused in the event of the ure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM all bear no responsibility whatsoever for your use of any Product outside of the prescribed ope or not in accordance with the instruction manual.
sys ma ins cor of	e Products are not designed or manufactured to be used with any equipment, device o stem which requires an extremely high level of reliability the failure or malfunction of which y result in a direct threat to human life or create a risk of human injury (such as a medica trument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel- ntroller or other safety device). ROHM shall bear no responsibility in any way for use of any the Products for the above special purposes. If a Product is intended to be used for any ch special purpose, please contact a ROHM sales representative before purchasing.
be	rou intend to export or ship overseas any Product or technology specified herein that may controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to tain a license or permit under the Law.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

# ROHM Customer Support System

http://www.rohm.com/contact/